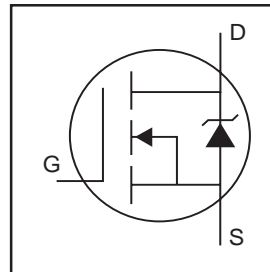


Features

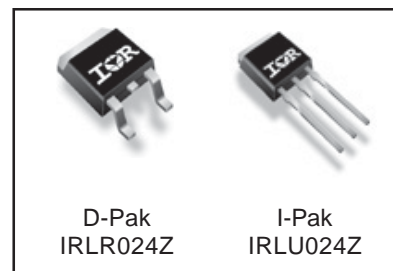
- Logic Level
- Advanced Process Technology
- Ultra Low On-Resistance
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free



$V_{DSS} = 55V$
$R_{DS(on)} = 58m\Omega$
$I_D = 16A$

Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ (Silicon Limited)	16	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	11	
I_{DM}	Pulsed Drain Current ①	64	
$P_D @ T_C = 25^\circ C$	Power Dissipation	35	W
	Linear Derating Factor	0.23	W/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
E_{AS} (Thermally limited)	Single Pulse Avalanche Energy ②	25	mJ
E_{AS} (Tested)	Single Pulse Avalanche Energy Tested Value ③	25	
I_{AR}	Avalanche Current ④	See Fig.12a, 12b, 15, 16	A
E_{AR}	Repetitive Avalanche Energy ⑤		mJ
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		

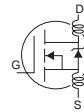
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	4.28	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount) ②	—	40	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

HEXFET® is a registered trademark of International Rectifier.

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.053	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	46	58	mΩ	$V_{GS} = 10V, I_D = 9.6A$ ③
		—	—	80		$V_{GS} = 5.0V, I_D = 5.0A$ ③
		—	—	100		$V_{GS} = 4.5V, I_D = 3.0A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	3.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	7.4	—	—	S	$V_{DS} = 25V, I_D = 9.6A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 55V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 55V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -16V$
Q_g	Total Gate Charge	—	6.6	9.9	nC	$I_D = 5.0A$
Q_{gs}	Gate-to-Source Charge	—	1.6	—		$V_{DS} = 44V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	3.9	—		$V_{GS} = 5.0V$ ③
$t_{d(on)}$	Turn-On Delay Time	—	8.2	—	ns	$V_{DD} = 28V$
t_r	Rise Time	—	43	—		$I_D = 5.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	19	—		$R_G = 28\Omega$
t_f	Fall Time	—	16	—		$V_{GS} = 5.0V$ ③
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	380	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	62	—		$V_{DS} = 25V$
C_{riss}	Reverse Transfer Capacitance	—	39	—		$f = 1.0MHz$
\hat{C}_{oss}	Output Capacitance	—	180	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz$
C_{oss}	Output Capacitance	—	50	—		$V_{GS} = 0V, V_{DS} = 44V, f = 1.0MHz$
$C_{oss\ eff.}$	Effective Output Capacitance	—	81	—		$V_{GS} = 0V, V_{DS} = 0V$ to 44V ④



Source-Drain Ratings and Characteristics

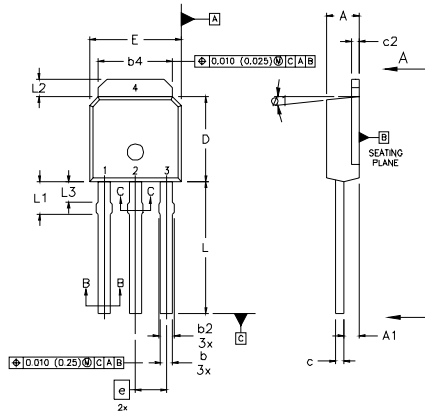
	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	16	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	64		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 9.6A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	16	24	ns	$T_J = 25^\circ\text{C}, I_F = 9.6A, V_{DD} = 28V$
Q_{rr}	Reverse Recovery Charge	—	11	17	nC	$di/dt = 100A/\mu s$ ③
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

IRLR/U024ZPbF

International
IR Rectifier

I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



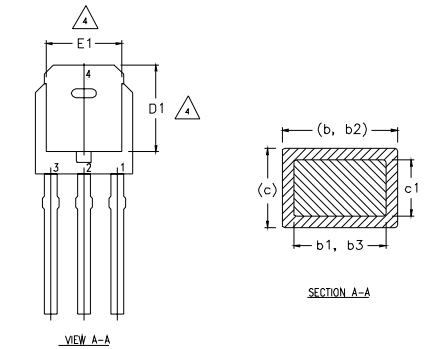
NOTES:

- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 4 THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
- 5 LEAD DIMENSION UNCONTROLLED IN L3.
- 6 DIMENSION b1, b3 APPLY TO BASE METAL ONLY.
- 7 OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA.
- 8 CONTROLLING DIMENSION : INCHES.

LEAD ASSIGNMENTS

HEXFET

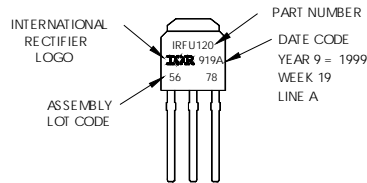
- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	0.086	.094	
A1	0.89	1.14	0.035	0.045	
b	0.64	0.89	0.025	0.035	
b1	0.64	0.79	0.025	0.031	4
b2	0.76	1.14	0.030	0.045	
b3	0.76	1.04	0.030	0.041	
b4	5.00	5.46	0.195	0.215	4
c	0.46	0.61	0.018	0.024	
c1	0.41	0.56	0.016	0.022	
c2	.046	0.86	0.018	0.035	
D	5.97	6.22	0.235	0.245	3, 4
D1	5.21	-	0.205	-	4
E	6.35	6.73	0.250	0.265	3, 4
E1	4.32	-	0.170	-	4
e	2.29		0.090 BSC		
L	8.89	9.60	0.350	0.380	
L1	1.91	2.29	0.075	0.090	
L2	0.89	1.27	0.035	0.050	4
L3	1.14	1.52	0.045	0.060	5
ø1	Ø	15'	Ø	15'	

I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120 WITH ASSEMBLY LOT CODE 5678 ASSEMBLED ON WW 19, 1999 IN THE ASSEMBLY LINE "A"
Note: "P" in assembly line position indicates "Lead-Free"



OR

